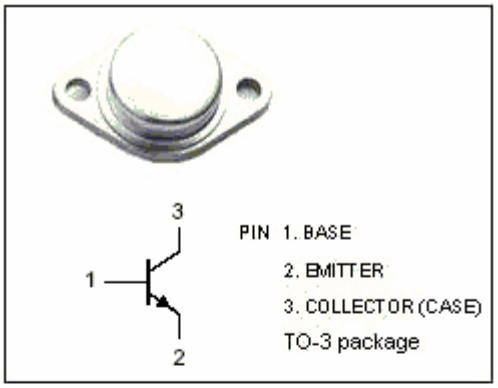
isc Silicon NPN Power Transistor BUX21

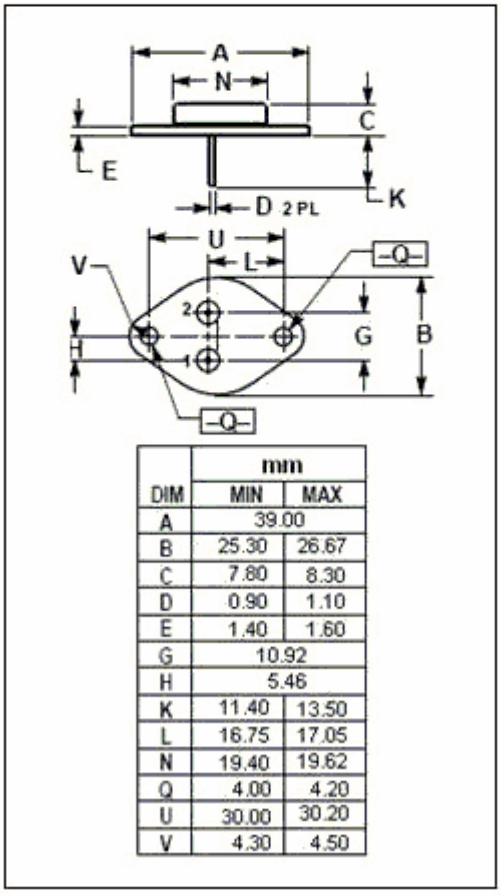
DESCRIPTION

- Low Collector Saturation Voltage-
- High Switching Speed
- High Current Current Capability

APPLICATIONS

- Desinged for use in switching and linear applications in military and industrial equipment.





DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.30
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.40	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	250	V
V_{CEX}	Collector-Emitter Voltage V_{BE}= -1.5V	250	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	40	A
I_{CM}	Collector Current-Peak	50	A
I_B	Base Current-Continuous	8	A
P_C	Collector Power Dissipation @T_C=25℃	350	W
T_j	Junction Temperature	200	℃
T_{stg}	Storage Temperature Range	-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	0.5	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 0.2A; I_B= 0	200			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 50mA; I_C= 0	7			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 12A; I_B= 1.2A			0.6	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 25A ;I_B= 3A			1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 25A ;I_B= 3A			1.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 160V; I_B= 0			3.0	mA
I_{CEX}	Collector Cutoff Current	V_{CE}= 250V;V_{BE}= -1.5V V_{CE}= 250V;V_{BE}= -1.5V;T_C=125℃			3.0 12.0	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			1.0	mA
h_{FE-1}	DC Current Gain	I_C= 12A ; V_{CE}= 2V	20		60	
h_{FE-2}	DC Current Gain	I_C= 25A ; V_{CE}= 4V	10			
f_T	Current-Gain—Bandwidth Product	I_C= 2A; V_{CE}= 15V, f_{test}= 10MHz	8			MHz
Switching Times						
t_{on}	Turn-on Time	I_C= 25A ;I_{B1}= 3A; V_{CC}= 100V			1.2	μs
t_s	Storage Time	I_C= 25A ;I_{B1}= -I_{B2}= 3A;V_{CC}= 100V			1.8	μs
t_f	Fall Time				0.4	μs